

REMARKS

At the outset, the Examiner is thanked for the thorough review and consideration of the pending application. The Office Action dated August 25, 2005 has been received and its contents carefully reviewed.

Applicants kindly acknowledge the allowance of claims 1-20 and 22-32. By this Response, claim 21 has been amended. No new matter has been added. Claims 1-32 are pending in the application. Reconsideration and withdrawal of the rejection in view of the above amendments and the following remarks are respectfully requested.

In the Office Action, claim 21 is rejected under 35 U.S.C. § 103(a) as being unpatentable over U.S. Patent No. 6,707,441, issued to Hebiguchi et al. (hereafter “Hebiguchi”) in view of Japanese Application No. 200002156, issued to Yamauchi (hereafter “Yamauchi”). Applicants respectfully traverse the rejection because neither Hebiguchi nor Yamauchi, analyzed alone or in any combination, teach or suggests the combined features recited in the claims of the present application. For example, Hebiguchi and Yamauchi fail to teach or suggest a thin film transistor “wherein the drain electrode has at least two portions uneven in width, the at least two uneven portions overlapping a gate electrode” as recited in claim 21 of the present application.

The Office Action concedes that Hebiguchi fails “to disclose the uneven width requirement of the drain electrode”. To remedy the deficient teachings of Hebiguchi, the Office Action relies upon the teachings in FIG. 3 of Yamauchi. Applicants respectfully submit Yamauchi fails to remedy the deficient teachings of Hebiguchi.

Yamauchi discloses “a source electrode 9 and a drain electrode 10 have a horizontally T-shaped part 91 or 101 in a region” (see, FIG. 3). However, Applicants note in the thin film transistor of Yamauchi, “the lengthwise parts 93 and 103 [of the source and drain electrodes, respectively] do not overlap with the gate electrode 5”. Thus, Yamauchi fails to teach “wherein the drain electrode has at least two portions uneven in width, the at least two uneven portions overlapping a gate electrode” as recited in independent claim 21 of the present application.

Because Yamauchi fails to teach this feature of claim 21, Yamauchi fails to remedy the deficient teachings of Hebiguchi. As such, no combination of Hebiguchi and Yamauchi

would provide a thin film transistor having all the combined features recited in independent claim 21. Accordingly, claim 21 is allowable over any combination of Hebiguchi and Yamauchi. Reconsideration and withdrawal of the rejection are respectfully requested.

Applicants believe the foregoing amendments and remarks place the application in condition for allowance and early, favorable action is respectfully solicited.

If for any reason the Examiner finds the application other than in condition for allowance, the Examiner is requested to call the undersigned attorney at (202) 496-7500 to discuss the steps necessary for placing the application in condition for allowance. All correspondence should continue to be sent to the below-listed address.

If these papers are not considered timely filed by the Patent and Trademark Office, then a petition is hereby made under 37 C.F.R. §1.136, and any additional fees required under 37 C.F.R. §1.136 for any necessary extension of time, or any other fees required to complete the filing of this response, may be charged to Deposit Account No. 50-0911. Please credit any overpayment to deposit Account No. 50-0911. A duplicate copy of this sheet is enclosed.

Dated: January 11, 2006

Respectfully submitted,

By Valerie P. Hayes
Valerie P. Hayes
Registration No.: 53,005
McKENNA LONG & ALDRIDGE LLP
1900 K Street, N.W.
Washington, DC 20006
(202) 496-7500
Attorneys for Applicant